

Plastic Darlington Complementary Silicon Power Transistors

...designed for general-purpose amplifier and low-speed switching applications.

- High DC Current Gain —
 $h_{FE} = 2000 \text{ (Typ) @ } I_C$
 $= 2.0 \text{ Adc}$
- Monolithic Construction with Built-in Base-Emitter Resistors to Limit Leakage Multiplication
- Choice of Packages —
 MJE700 and MJE800 series

MAXIMUM RATINGS

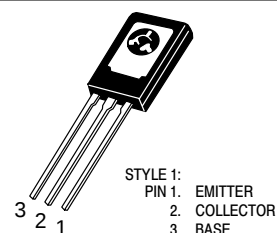
Rating	Symbol	MJE700 MJE800	MJE702 MJE703 MJE802 MJE803	Unit
Collector–Emitter Voltage	V _{CEO}	60	80	Vdc
Collector–Base Voltage	V _{CB}	60	80	Vdc
Emitter–Base Voltage	V _{EB}	5.0		Vdc
Collector Current	I _C	4.0		Adc
Base Current	I _B	0.1		Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	CASE 77		Watts W/°C
		40 0.32		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case CASE 77 TO-220	$R_{\theta JC}$	3.13 2.50	$^\circ\text{C/W}$

PNP
MJE700
MJE702
MJE703
NPN
MJE800
MJE802
MJE803

**4.0 AMPERE
 DARLINGTON
 POWER TRANSISTORS
 COMPLEMENTARY
 SILICON
 40 WATT
 50 WATT**



**CASE 77-08
 TO-225AA TYPE
 MJE700-703
 MJE800-803**

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

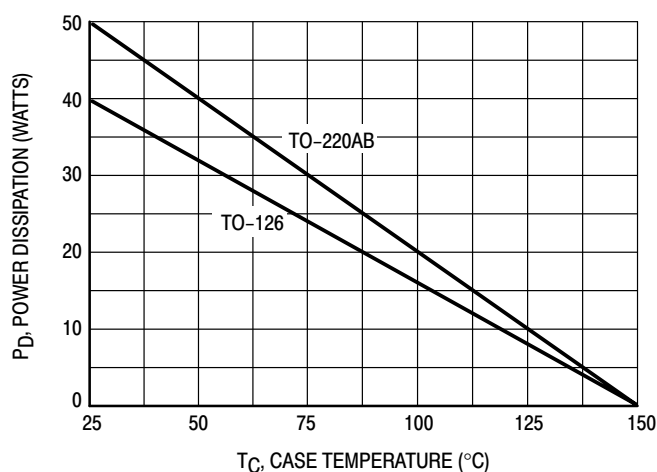


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (1) ($I_C = 50\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	60 80	— —	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 80\text{ Vdc}$, $I_B = 0$)	I_{CEO}	— —	100 100	μAdc
Collector Cutoff Current ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$) ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$, $T_C = 100^\circ\text{C}$)	I_{CBO}	— —	100 500	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	2.0	mAdc

ON CHARACTERISTICS

DC Current Gain (1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	MJE700, MJE702, MJE800, MJE802 MJE703, MJE803 All devices	h_{FE}	750 750 100	— — —	—
Collector-Emitter Saturation Voltage (1) ($I_C = 1.5\text{ Adc}$, $I_B = 30\text{ mAdc}$) ($I_C = 2.0\text{ Adc}$, $I_B = 40\text{ mAdc}$) ($I_C = 4.0\text{ Adc}$, $I_B = 40\text{ mAdc}$)	MJE700, MJE702, MJE800, MJE802 MJE703, MJE803 All devices	$V_{CE(sat)}$	— — —	2.5 2.8 3.0	Vdc
Base-Emitter On Voltage (1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	MJE700, MJE702, MJE800, MJE802 MJE703, MJE803 All devices	$V_{BE(on)}$	— — —	2.5 2.5 3.0	Vdc

DYNAMIC CHARACTERISTICS

Small-Signal Current Gain ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	h_{fe}	1.0	—	—
---	----------	-----	---	---

(1) Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

R_B & R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS

D_1 , MUST BE FAST RECOVERY TYPE, e.g.:

1N5825 USED ABOVE $I_B \approx 100$ mA

MSD6100 USED BELOW $I_B \approx 100$ mA

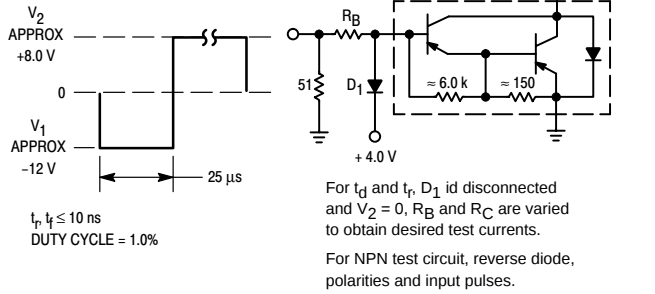


Figure 2. Switching Times Test Circuit

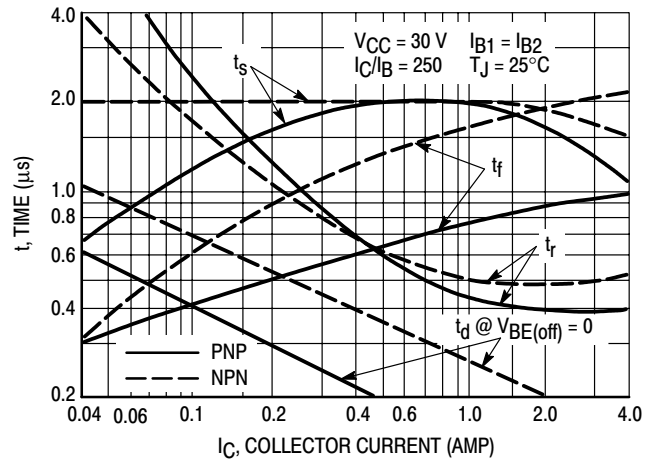


Figure 3. Switching Times

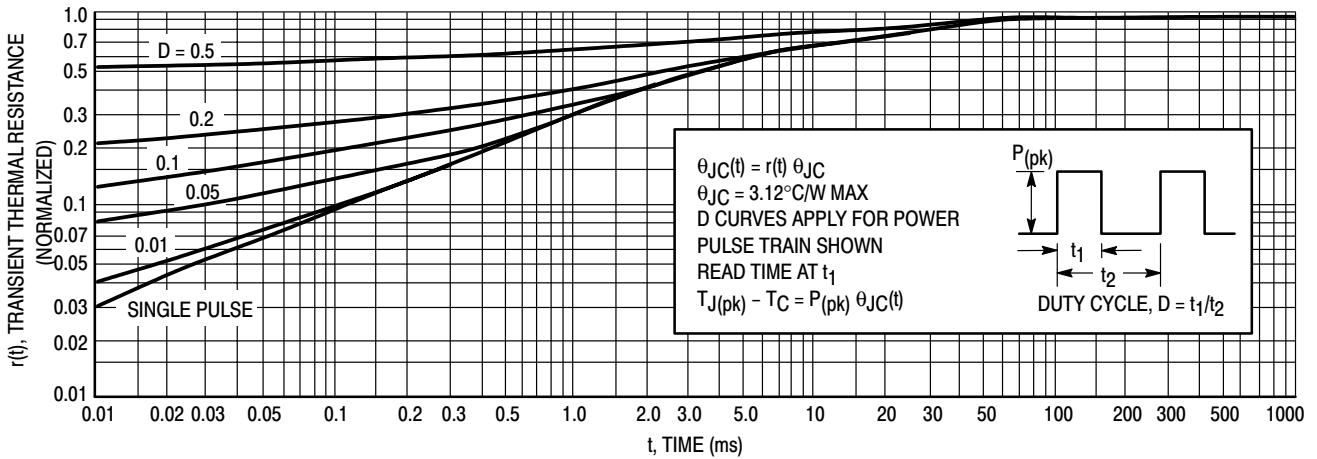


Figure 4. Thermal Response (MJE700, 800 Series)

ACTIVE-REGION SAFE-OPERATING AREA

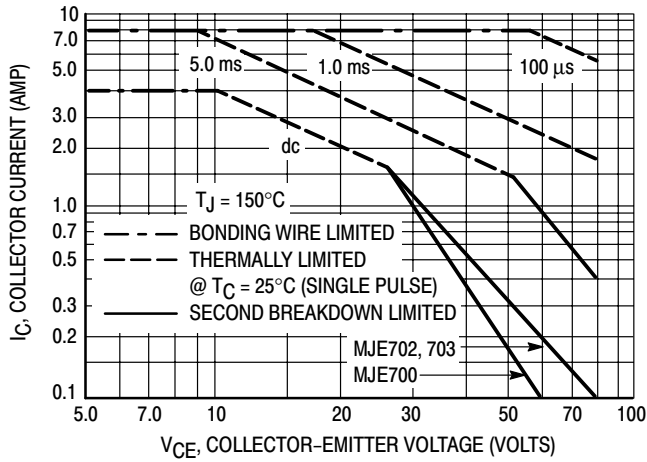


Figure 5. MJE700 Series

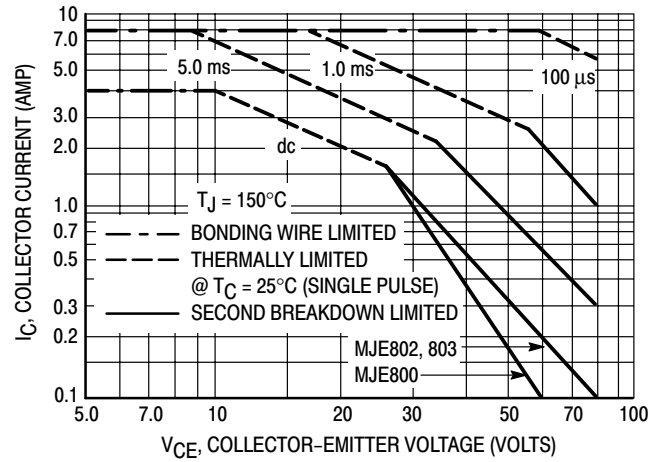


Figure 6. MJE800 Series

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5 and 6 are based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown

pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

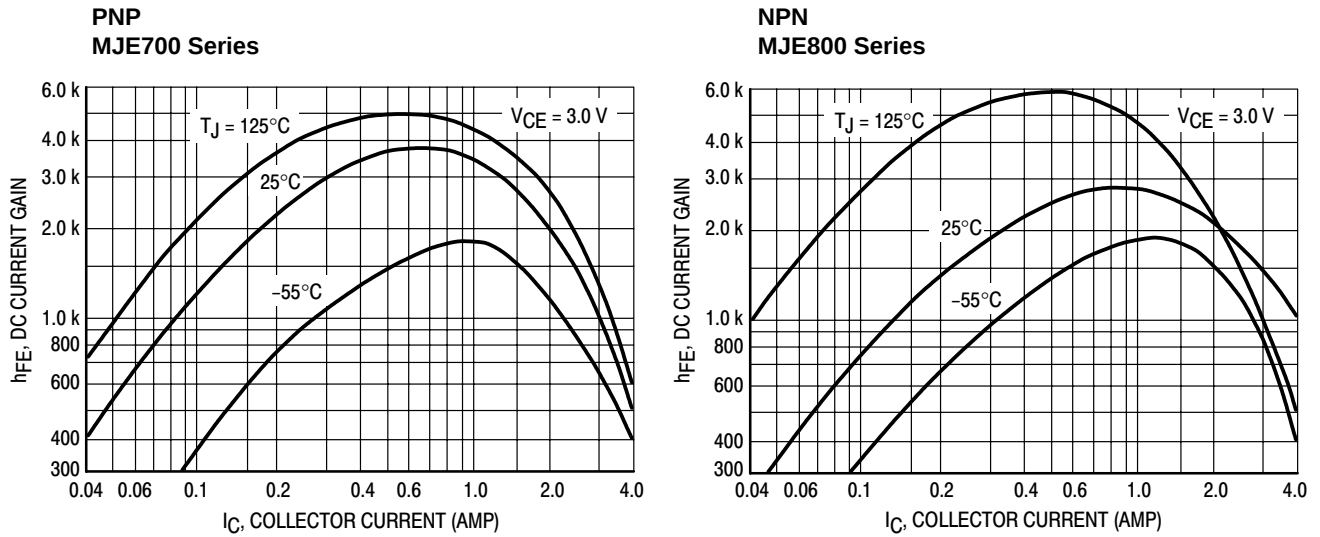


Figure 7. DC Current Gain

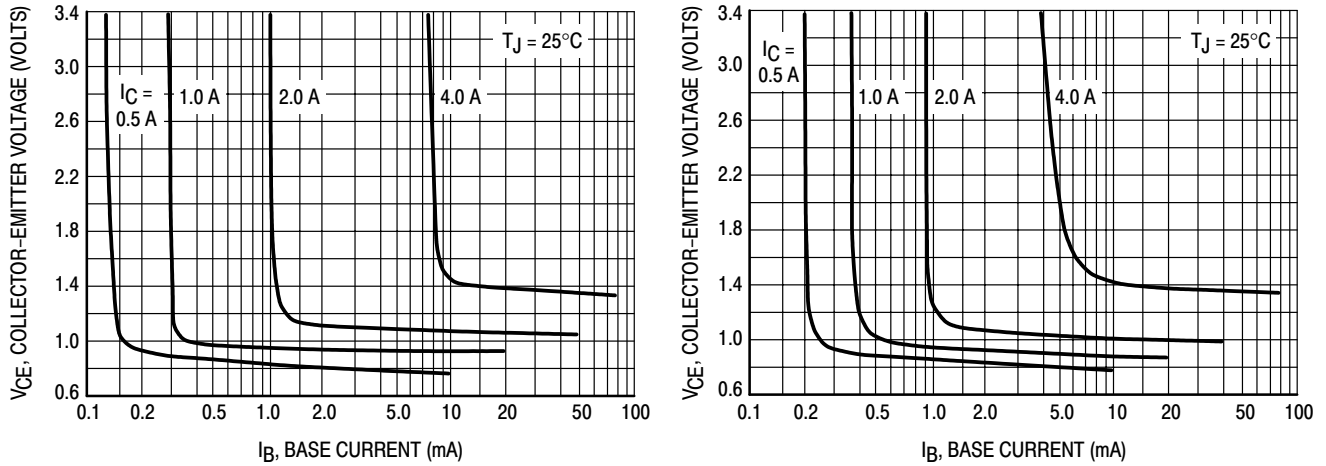


Figure 8. Collector Saturation Region

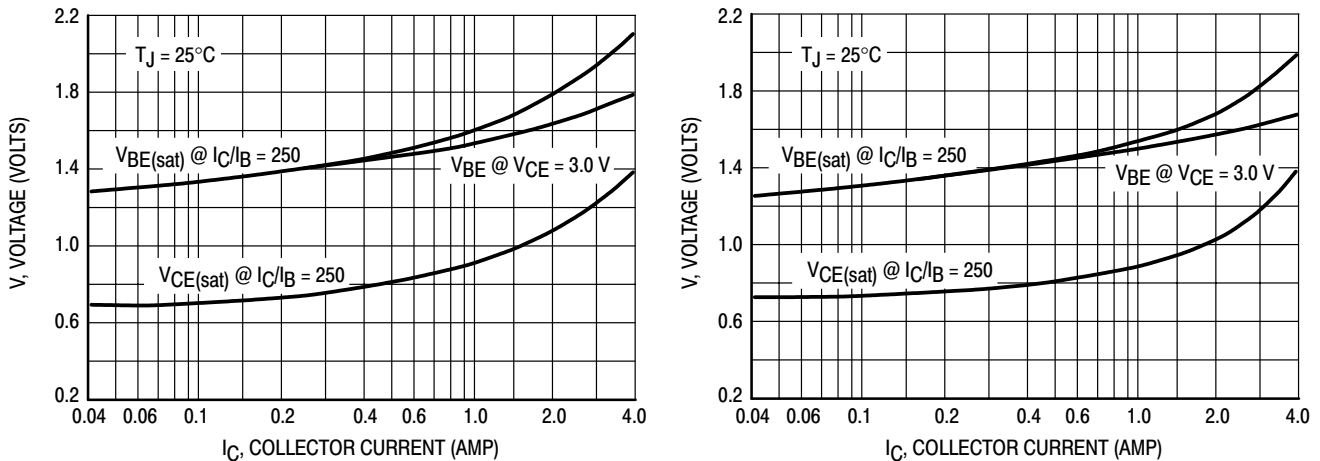
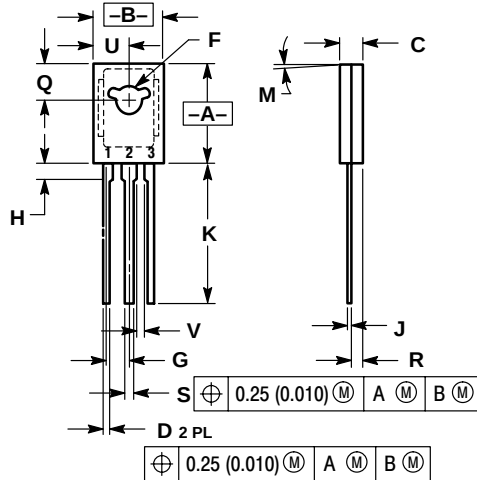


Figure 9. "On" Voltages

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

PACKAGE DIMENSIONS

TO-225AA CASE 77-09 ISSUE W



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

- STYLE 1:
1. EMITTER
 2. COLLECTOR
 3. BASE

Notes

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.